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Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: August 13, 2001
(use as many sheets as necessary)

Sheet	1	of	3

Complete if Known	
Application Number	To Be Assigned
Filing Dat	August 13, 2001
First Nam d Inv ntor	Andrew J. WALKER et al.
Group Art Unit	~~Unassigned~~ 2827
Examiner Name	~~Unassigned~~
Attorney Docket Number	035905/0103

Jc879 U.S. PTO 09/927642 08/13/01

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	5,966,603		Eitan	10/12/1999	
	A2	6,028,326		Uochi et al.	2/22/2000	
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	A25	JP	5-082787			4/2/1993		X

Examiner Signature		Date Considered	Y-19-03

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				Filing Dat	August 13, 2001
				First Named Invent r	Andrew J. WALKER et al.
Date Submitted: August 13, 2001				Group Art Unit	~~Unassigned~~ 2829
(use as many sheets as necessary)				Examiner Name	~~Unassigned~~ Per F
Sheet	2	of	3	Attorney Docket Number	035905/0103

JC879 U.S. PTO 09/927642 08/13/01

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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Examiner Signature		Date Considered	4-16-03

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Sheet | 3 | of | 3

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Filing Dat	August 13, 2001
First Nam d Inv nt r	Andrew J. WALKER et al.
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	035905/0103

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Examiner Signature	Eun Rest	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: November 26, 2001

(use as many sheets as necessary)

Sheet 1 of 7

Complete if Kn[redacted]n	
Applicati n Number	09/927,642
Filing Dat	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2618~~ 2829
Examiner Name	Unassigned Pert
Attorney Docket Number	035905-0103

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	Sun Pert	Date Considered	4-18-03

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Date Submitted: November 26, 2001

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Sheet 2 of 7

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Application Number	09/927,642
Filing Dat	08/13/2001
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OIPE NOV 27 2001 PATENT & TRADEMARK OFFICE

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		U.S. Patent Document				
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	A112	3,671,948		Cassen et al.	6/20/1972	
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Examiner Signature	Evan Pert	Date Considered	4-18-03

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U.S. Patent and Trademark Office: [redacted] DEPARTMENT OF COMMERCE

Substitute for form 1449B/PTO				*Complete if Kn[redacted]*	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	09/927,642
Date Submitted: November 27, 2001				**Filing Date**	08/13/2001
				First Named Inventor	Andrew J. WALKER et al.
(use as many sheets as necessary)				Group Art Unit	~~2818~~ 2829
				Examiner Name	Unassigned Pert
Sheet	4	of	7	Attorney Docket Number	~~035905-0103~~

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
	A124	BOAZ EITAN et al.: "Alternate Metal Virtual Ground (AMG) - A New Scaling Concept for Very High-Density EPROM's," IEEE Electron Device Letters, pgs. 450-452, Vol. 12, No. 8, August 1991, IEEE	
	A125	BOAZ EITAN et al.: "Multilevel Flash cells and their Trade-offs," IEEE Electron Device Letters , pgs. 169-172, 1996, IEEE	
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	A128	G.K. GIUST et al.: "Laser-Processed Thin-Film Transistors Fabricated from Sputtered Amorphous-Silicon Films," IEEE Transactions on Electron Devices, pgs. 207-213, Vol. 47, No. 1, January 2000, IEEE	
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Examiner Signature	Evan Pert	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: November 26, 2001

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Sheet 5 of 7

Complete if Kn[redacted]	
Application Number	09/927,642
Filing Dat	08/13/2001
First Nam d Inventor	Andrew J. WALKER et al.
Group Art Unit	2818
Examiner Name	Unassigned
Attorney Docket Number	035905-0103

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	A133	J. ESQUIVEL et al. "High Density Contactless, Self Aligned EPROM Cell Array Technology," Texas Instruments (Dallas), IEDM 86, pgs. 592-595, 1986, IEEE	
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EP	A136	JOHAN H. KLOOTWIJK et al.: "Deposited Inter-Polysilicon Dielectrics for Nonvolatle Memories," IEEE Transactions on Electron Devices , pgs. 1435-1445, Vol. 46, No. 7, July 1999, IEEE	
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Examiner Signature	[signature]	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: November 26, 2001

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Sheet 6 of 7

Complete if Known	
Application Number	09/927,642
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Peralta
Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
EP	A142	N.D. YOUNG et al.: "The Fabrication and Characterization of EEPROM Arrays on Glass Using a Low-Temperature Poly-Si TFT Process," IEEE Transactions on Electron Devices, pgs. 1930-1936, Vol. 43, No. 11, November 1996, IEEE	
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EP	A147	SEUNGHEON SONG et al.: "High Performance Transistors with State-of-the-Art CMOS Technologies," IEDM 99, pgs. 427-430, 1999, IEEE	
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Substitute for form 1449B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	09/927,642
Date Submitted: November 27, 2001				**Filing Date**	08/13/2001
				First Named Inventor	Andrew J. WALKER et al.
(use as many sheets as necessary)				Group Art Unit	2818 2829 Per T
				Examiner Name	Unassigned
Sheet	7	of	7	Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
	A151	HONGMEI WANG et al.: "Super Thin-Film Transistor with SOI CMOS Performance Formed by a Novel Grain Enhancement Method," IEEE Transactions on Electron Devices, pgs. 1580-1586, Vol. 47, No. 8, August 2000, IEEE	
	A152	MARVIN H. WHITE et al." "On the Go With Sonos," Circuit & Devices, pgs. 22-31, July 2000, IEEE	
	A153	B.J. WOO et al.: "A Novel Memory Cell Using Flash Array Contactless Eprom (Face) Technology," IEDM, pgs. 90-93, 1990, IEEE	
	A154	QI XIANG et al.: "Deep sub-100 nm CMOS with Ultra Low Gate Sheet Resista NiSi," VLSI Technology, 2000. Digest of Technical Paper Symposium on... pgs. 76-77, IEEE Xplore, June 13-15, 2000	
	A155	QI XIANG et al."Deep Sub-100nm CMOS with Ultra Low Gate Sheet Resistance by NiSi," IEEE, pgs. 76-77, 2000, Symposium on VLSI Technology Digest of Technical Papers	
	A156	QIUXIA XU et al.: "New Ti-SALICIDE Process Using Sb and Ge Preamorphization for Sub-0.2 μm CMOS Technology," IEEE Transactions on Electron Devices, pgs. 2002-2009, Vol. 45, No. 9, September 1998, IEEE	
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	A158	QI XIANG et al.: "Deep Sub-100nm CMOS with Ultra Low Gate Sheet Resistance by NiSi," pgs. 76-77, 2000 Symposium on VLSI Technology Digest of Technical Papers	
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	A160	DIETMAR GOGL et al.: "A 1-Kbit EEPROM in SIMOX Technology for High-Temperature Applications up to 250° C," IEEE Journal of Solid-State Circuits, October 2000, Vol. 35, No. 10, IEEE	

Examiner Signature		Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: April 1, 2002

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Sheet 1 of 1

Complete if Known	
Application Number	09/927,642
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	2818 2829
Examiner Name	~~Unassigned~~ Per T
Attorney Docket Number	035905-0103

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (*if known*)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
ER	A161	6,208,545		Leedy	3/27/2001	

FOREIGN PATENT DOCUMENTS

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: June 27, 2002

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Sheet 1 of 1

Complete if Known	
Application Number	09/927,642
Filing Date	08/13/2001
First Named Inventor	Andrew J. Walker al.
Group Art Unit	~~2818~~ 2829
Examiner Name	Not ~~Assigned~~ Pert
Attorney Docket Number	035905-0103

U.S. PATENT DOCUMENTS

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EP	C1	5,283,468		Kondo	FE-01-1994	

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EP	C3	LAY, RICHARD, "TRW Develops Wireless Multiboard Interconnect System", Electronic Engineering Times, November 5, 1994.	

Examiner Signature	Evan Pert	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: September 20, 2002

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Sheet 1 of 1

Complete if Known	
Application Number	09/927,642
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Pert
Attorney Docket Number	035905-0103

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EP	B1	5,973,356		Noble	10/26/1999	
EP	B2	0055838A1		Walker, et al	12/27/2001	
EP	B3	0028541A1		Lee, et al	03/07/2002	

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Examiner Signature	Evan Pert	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

#12

Date Submitted: 02-05-03

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Sheet 1 of 1

Complete if Known	
Application Number	09/927,642
Filing Date	08/13/2001
First Named Inventor	Andrew J. Walker
Group Art Unit	2829
Examiner Name	Evan T. Pert
Attorney Docket Number	035905-0103

U.S. PATENT DOCUMENTS

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EP	B4	WADA Y. et al., "Active-Body-Bias SOI-CMOS Driver Circuits", June 1997 Symposium on VLSI Circuits Digest of Technical Papers, pages 29-30	Y

Examiner Signature	Evan Pert	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: June 11, 2002

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Sheet 1 of 7

Complete if Known	
Application Number	09/927,462
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	Unassigned Peri
Attorney Docket Number	035905-0103

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
EP	B1	4,500,905		Shibata		
EP	B2	6,185,122		Johnson et al.		
EP	B3	3,414,892		McCormack et al.	12/13/1968	
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EP	B5	4,535,424		Reid		
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Examiner Signature	Eva Perl	Date Considered	4-18-03

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Sheet 2 of 7

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Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Pert
Attorney Docket Number	035905-0103

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Examiner Signature	Pert	Date Considered	4-18-03

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3 of 7

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First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2825
Examiner Name	~~Unassigned~~ Pert
Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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Examiner Signature	Evan Pert	Date Considered	4-18-03

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Sheet 4 of 7

Complete if Known	
Application Number	09/927,462
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Port
Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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Examiner Signature	Evan Port	Date Considered	4-15-03

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Sheet 5 of 7

Complete if Known	
Application Number	09/927,462
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Pert
Attorney Docket Number	035905-0103

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Examiner Signature	Evan Pert	Date Considered	4-18-03

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 6 of 7

Complete if Known	
Application Number	09/927,462
Filing Date	08/13/2001
First Named Inventor	Andrew J. WALKER et al.
Group Art Unit	~~2818~~ 2829
Examiner Name	~~Unassigned~~ Rutt
Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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Examiner Signature	Eva Rutt	Date Considered	4-18-03

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Sheet 7 of 7

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Examiner Name	~~Unassigned~~ Peralta
Attorney Docket Number	035905-0103

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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Examiner Signature		Date Considered	4-16-03

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